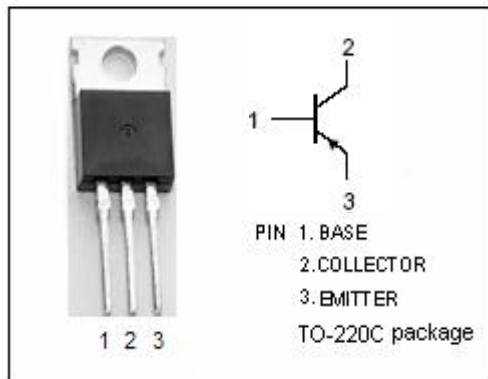


isc Silicon PNP Power Transistor
BD944/946/948
DESCRIPTION

- DC Current Gain-
: $h_{FE} = 85(\text{Min}) @ I_C = -500\text{mA}$
- Complement to Type BD943/945/947
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

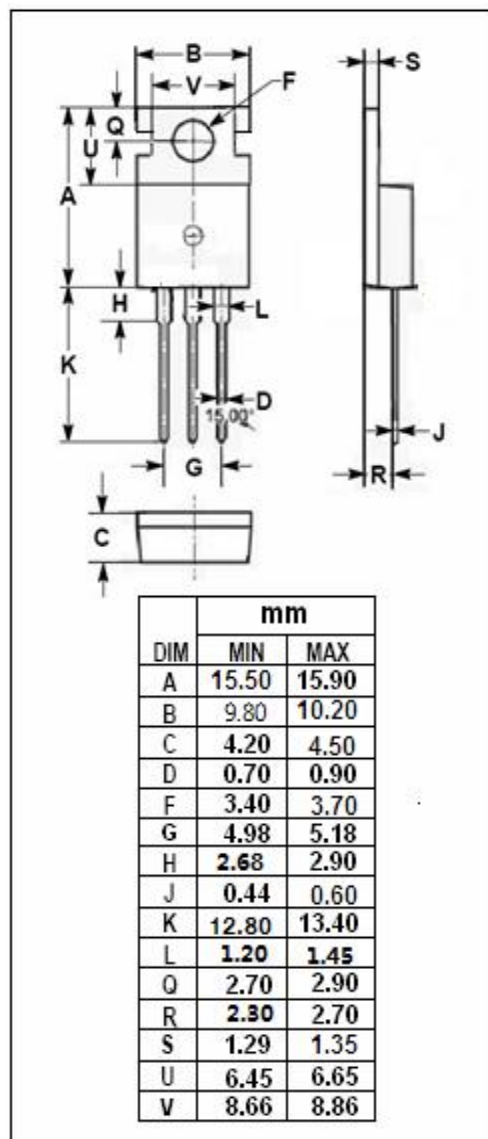
- Designed for use in audio output stages and general purpose amplifier applications.


ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BD944	-22	V
		BD946	-32	
		BD948	-45	
V_{CEO}	Collector-Emitter Voltage	BD944	-22	V
		BD946	-32	
		BD948	-45	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-5	A	
I_{CM}	Collector Current-Peak	-8	A	
I_B	Base Current-Continuous	-1	A	
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	40	W	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.12	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	70	$^\circ\text{C/W}$



isc Silicon PNP Power Transistor
BD944/946/948
ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-Emitter Sustaining Voltage	BD944	I _C = -30mA ; I _B = 0	-22			V
		BD946		-32			
		BD948		-45			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	BD944/946	I _C = -2A; I _B = -0.2A			-0.5	V
		BD948	I _C = -3A; I _B = -0.3A			-0.7	
V _{BE(on)}	Base-Emitter On Voltage	BD944/946	I _C = -2A; V _{CE} = -1V			-1.1	V
		BD948	I _C = -3A; V _{CE} = -1V			-1.3	
I _{CBO}	Collector Cutoff Current		V _{CB} = V _{CB0max} ; I _E = 0 V _{CB} = V _{CB0max} ; I _E = 0, T _J =150°C			-0.05 -1	mA
I _{CEO}	Collector Cutoff Current	BD944	V _{CE} = -15V; I _B = 0			-0.1	mA
		BD946	V _{CE} = -20V; I _B = 0				
		BD948	V _{CE} = -25V; I _B = 0				
I _{EBO}	Emitter Cutoff Current		V _{EB} = -5V; I _C = 0			-0.2	mA
h _{FE-1}	DC Current Gain		I _C = -10mA ; V _{CE} = -5V	25			
h _{FE-2}	DC Current Gain		I _C = -500mA ; V _{CE} = -1V	85		475	
h _{FE-3}	DC Current Gain	BD944/946	I _C = -2A ; V _{CE} = -1V	50			
		BD948		40			
h _{FE-4}	DC Current Gain-- Only For BD948		I _C = -3A ; V _{CE} = -1V	30			
f _T	Current-Gain—Bandwidth Product		I _C = -250mA ; V _{CE} = -1V	3			MHz

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.